

ELECTRONIC INFORMATION DISCLOSURE STATEMENT

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Title of Invention	METHOD OF FORMING FET SILICIDE GATE STRUCTURES INCORPORATING INNER SPACERS
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Application Number :

Confirmation Number:

First Named Applicant: Victor Ku

Attorney Docket Number: FIS920030341

Art Unit:

Examiner:

Search string: (6376888 or 6373111 or 5619057 or 6501131 or 6355531 or 4745079 or 20030119292 or 20020179975 or 20020086504 or 20020123189 or 20030011037 or 20030075766).pn

US Patent Documents

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
	1	6376888	2002-04-23	Tsunashima et al.			
	2	6373111	2002-04-16	Zheng et al.			
	3	5619057	1997-04-08	Komatsu			
	4	6501131	2002-12-31	Divakaruni et al.			
	5	6355531	2002-03-12	Mandelman et al.			
	6	4745079	1988-05-17	Pfiester			

US Published Applications

Note: Applicant is not required to submit a paper copy of cited US Published Applications

init	Cite.No.	Pub. No.	Date	Applicant	Kind	Class	Subclass
	1	20030119292	2003-06-26	Lee et al.			
	2	20020179975	2002-12-05	Wakabayashi et al.			
	3	20020086504	2002-07-04	Park et al.			
	4	20020123189	2002-09-05	Cha et al.			
	5	20030011037	2003-01-16	Chau et al.			
	6	20030075766	2003-04-24	Lin et al.			

Signature

Examiner Name	Date